



## Maximum Ratings



**Electrical Characteristics of the IGBT**  $T_j = 25$  unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.
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**Electrical Characteristics of the Diode**  $T_j=25$  unless otherwise specified

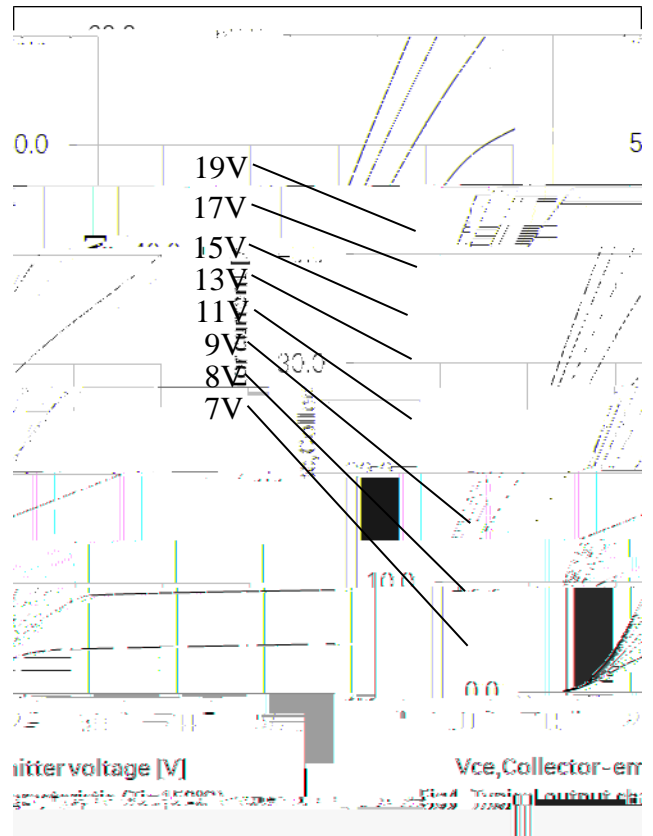
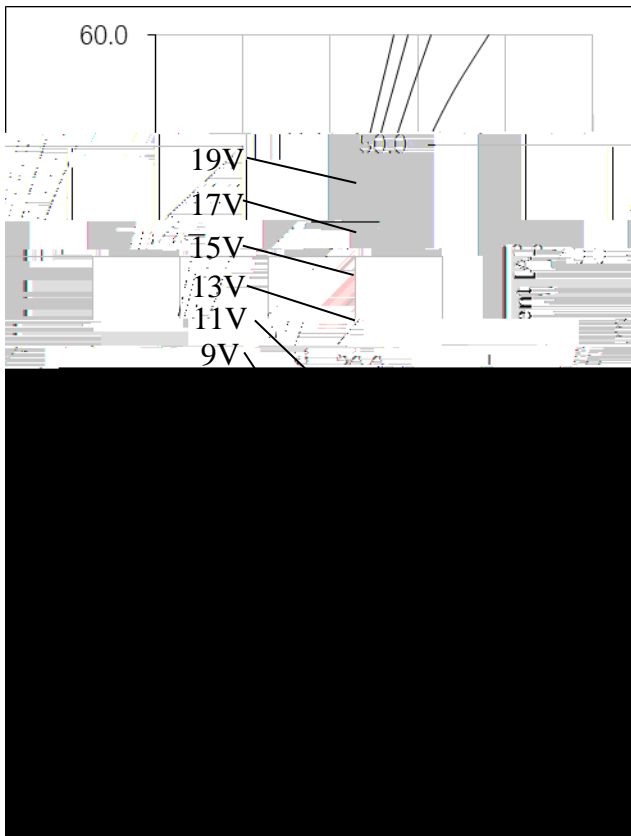
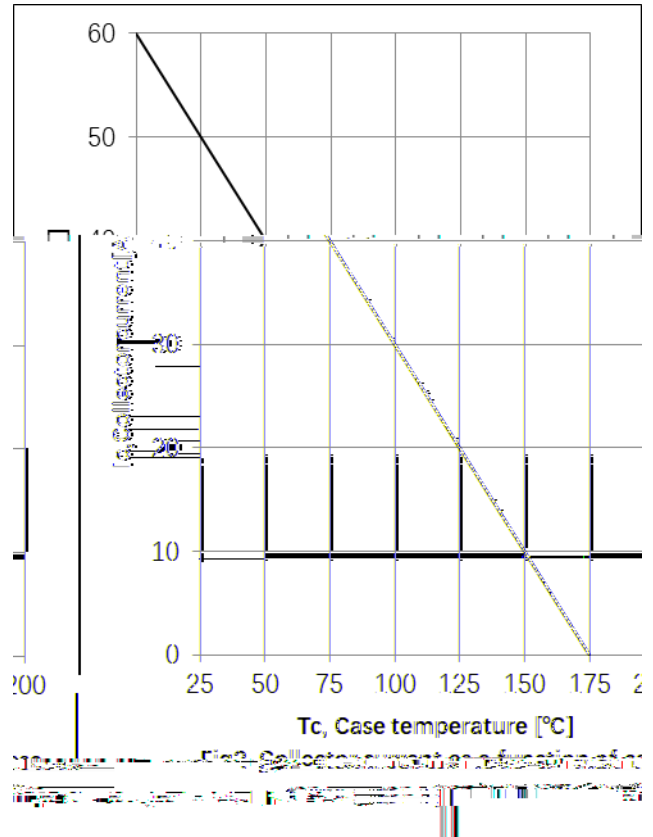
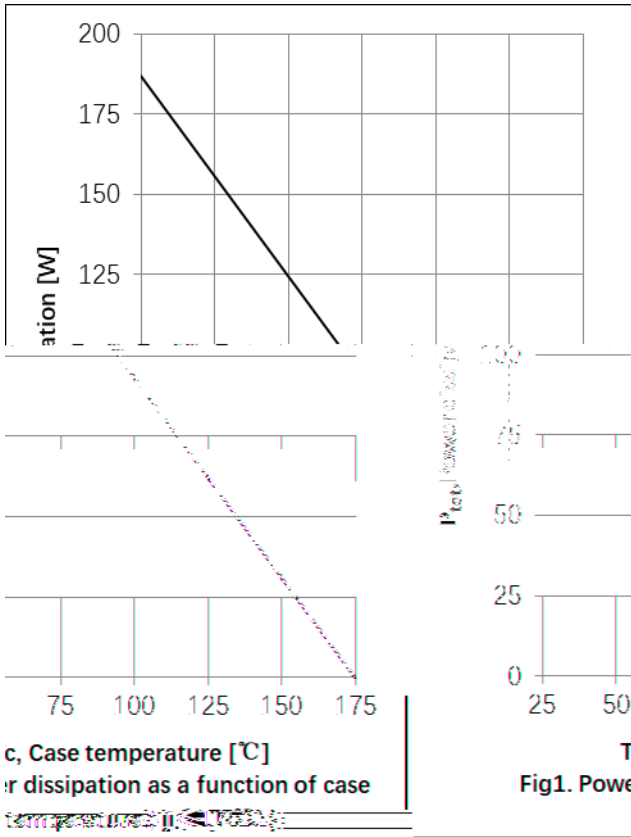
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Diode Forward Voltage	$V_F$	$I_F=30A$ $T_j=25^{\circ}C$ , $T_j=125^{\circ}C$ $T_j=150^{\circ}C$		1.90 1.85 1.75	2.60	V

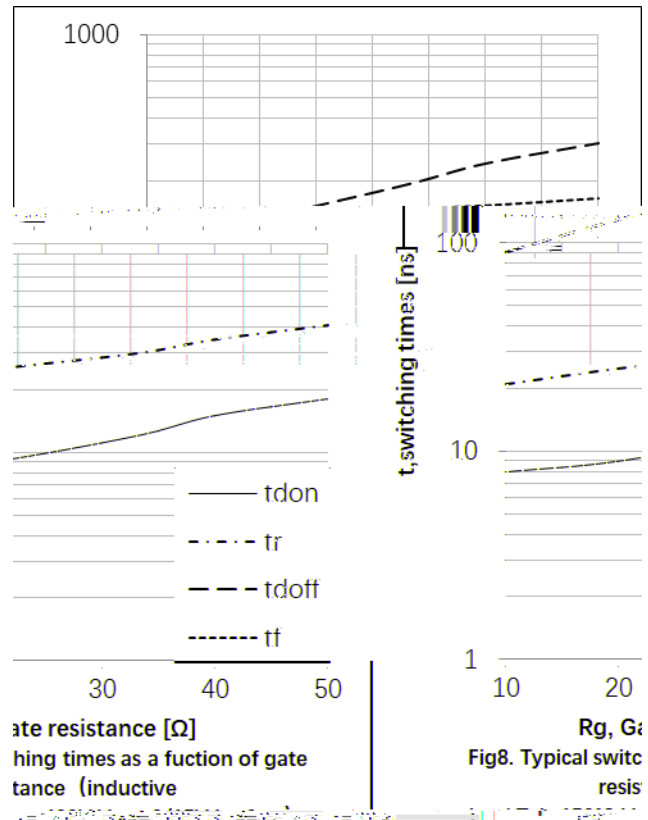
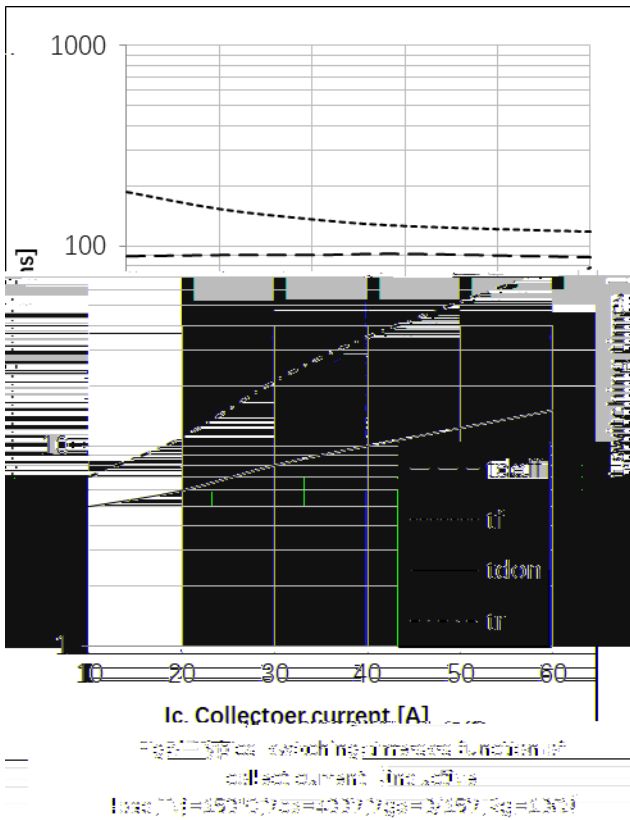
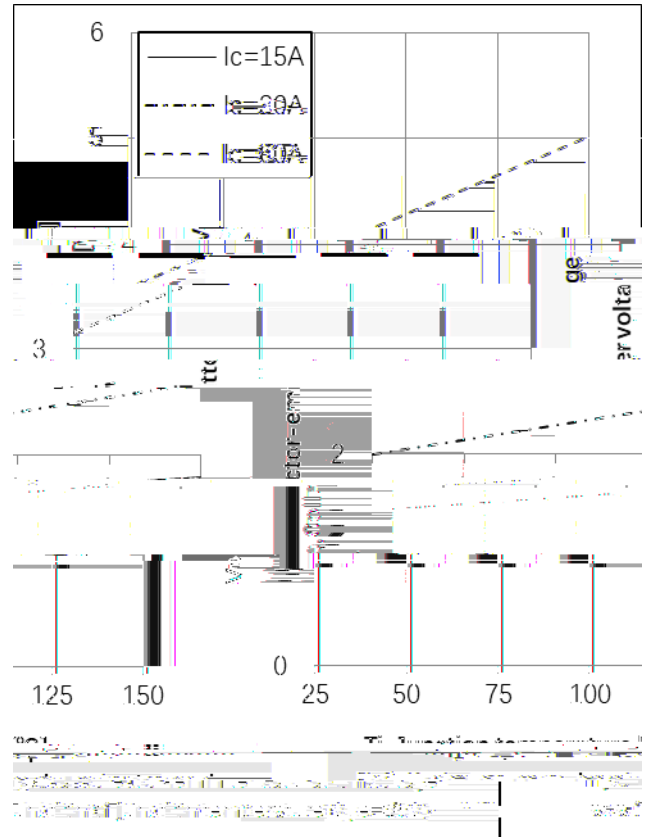
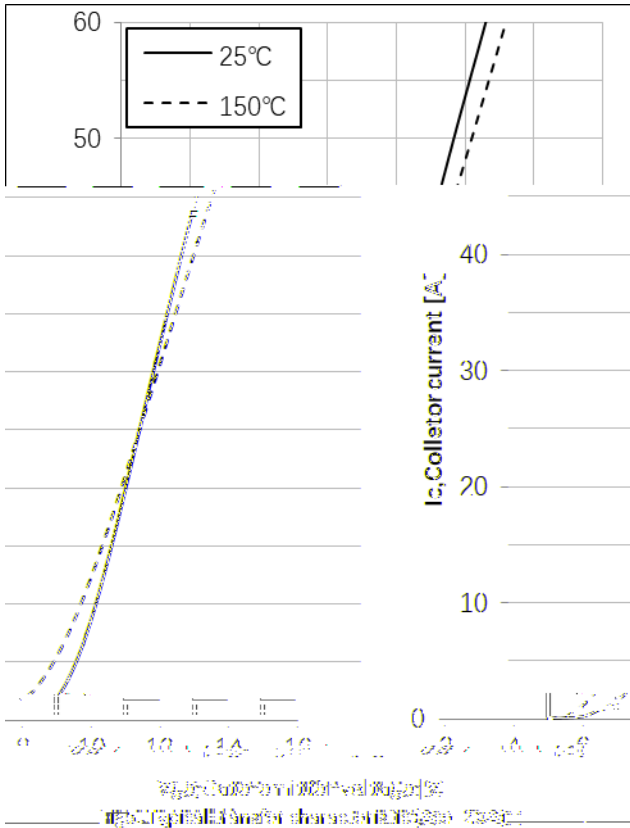
**Switching Characteristic, Inductive Load**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic , at <math>T_j=25</math></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{CC}=400V, I_C=30A,$ $V_{GE}=0V\sim 15V,$ $R_g=10, L_s=60nH$	-	8	-	ns
Rise Time	$t_r$		-	22	-	ns
Turn-on Energy	$E_{on}$		-	1.05	-	mJ
Turn-off Delay Time	$t_{d(off)}$		-	80	-	ns
Fall Time	$t_f$		-	-	20.52	-



**DGW30N65CTH**





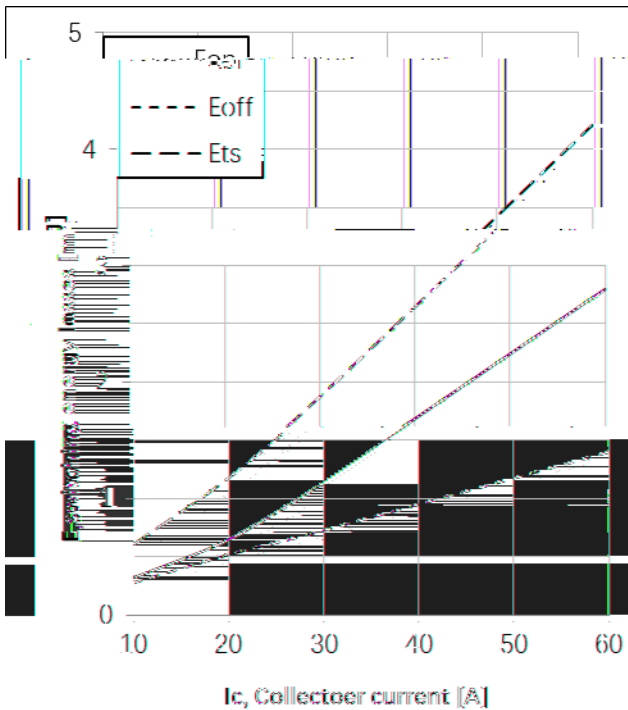
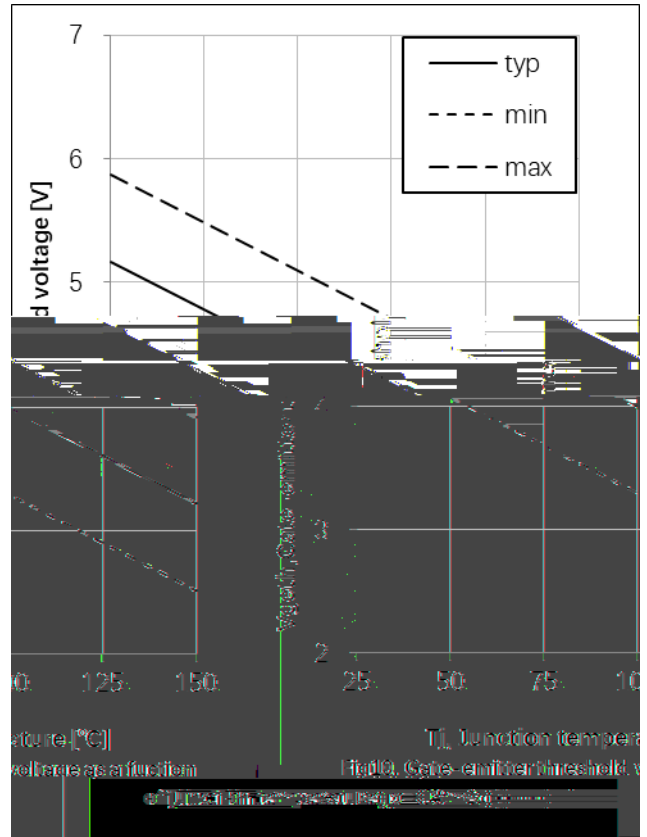
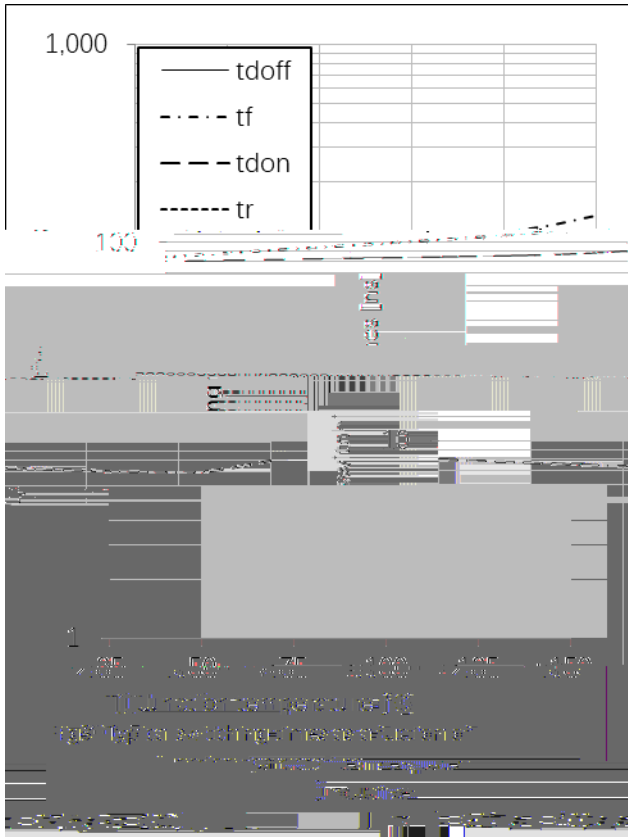


Fig11. Typical switching energy losses as a function of collector current

$I_{base} = 1.0 A, V_{ce} = 400 V, V_{gs} = 15.0 V, Q_g = 1.0 nC$

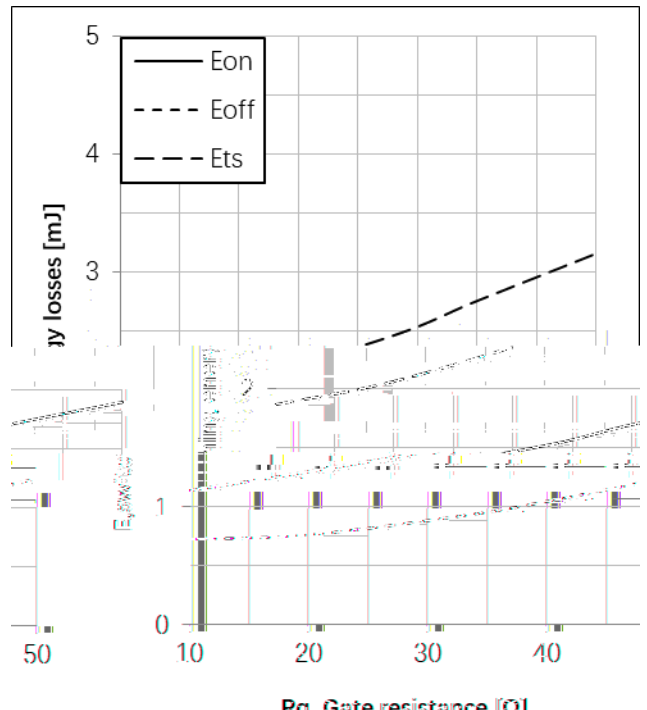
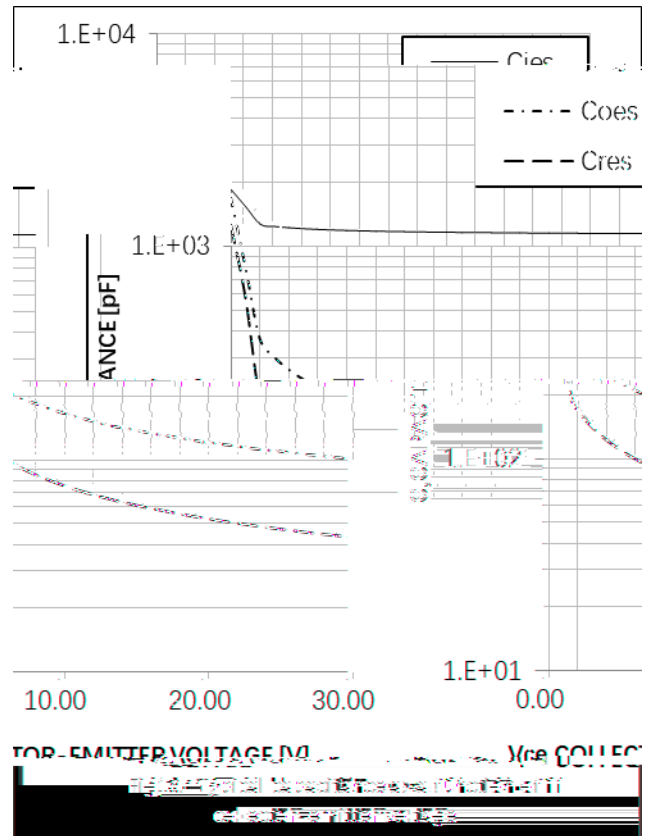
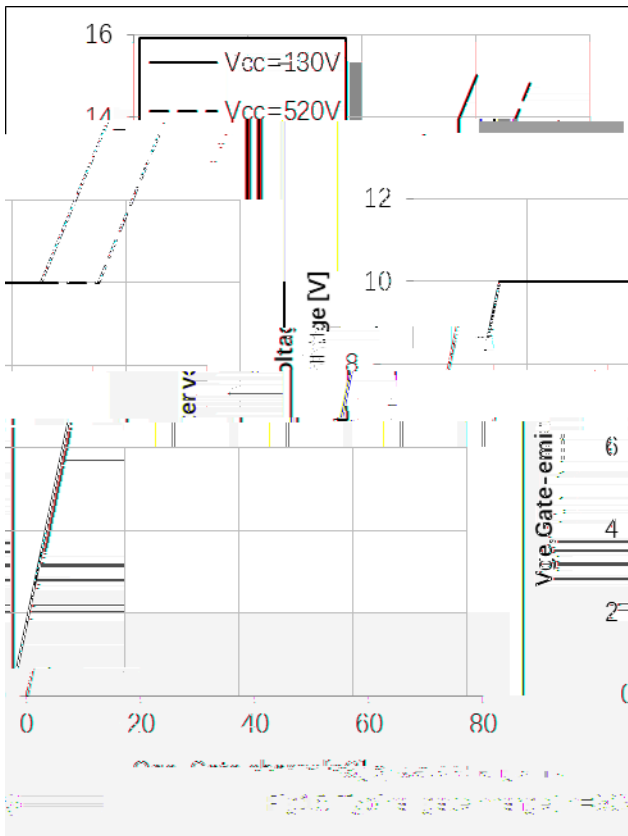
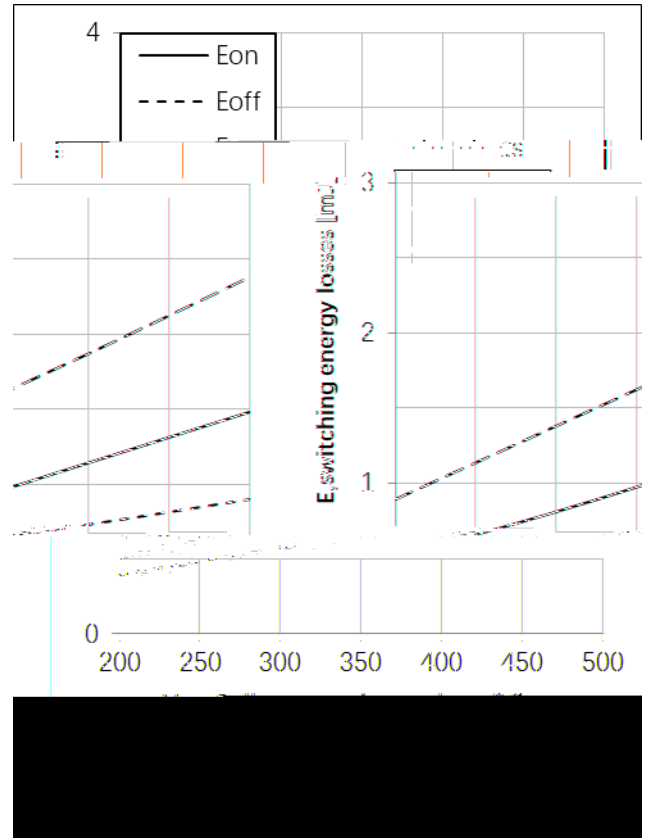
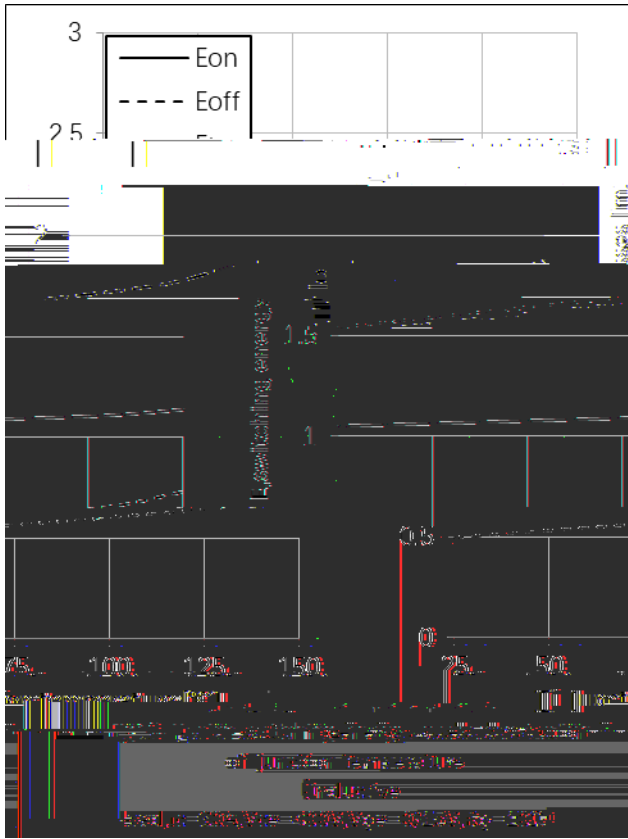


Fig12. Typical switching energy losses as a function of gate resistance (inductive load)

$V_{ce} = 400 V, I_{load} = 10 A, V_{gs} = 15.0 V, Q_g = 1.0 nC$



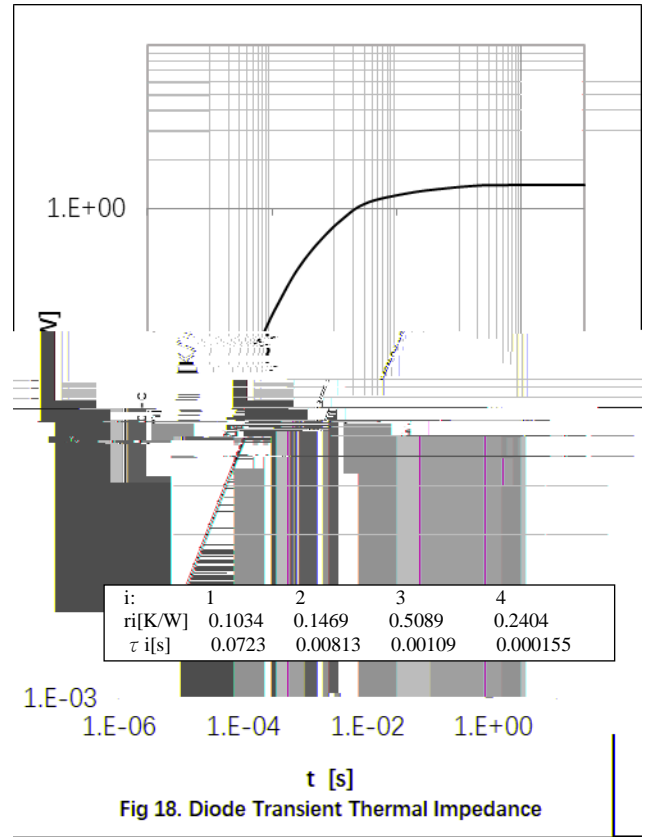
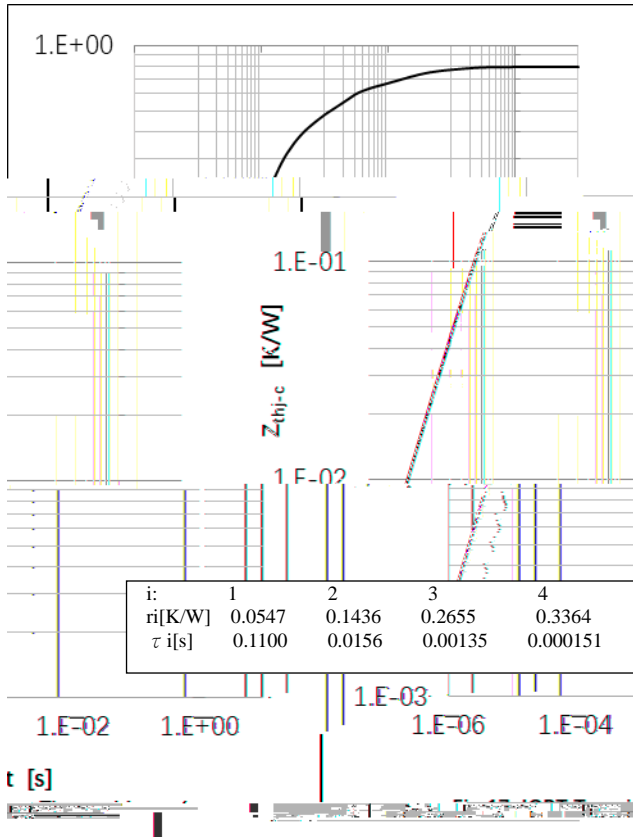
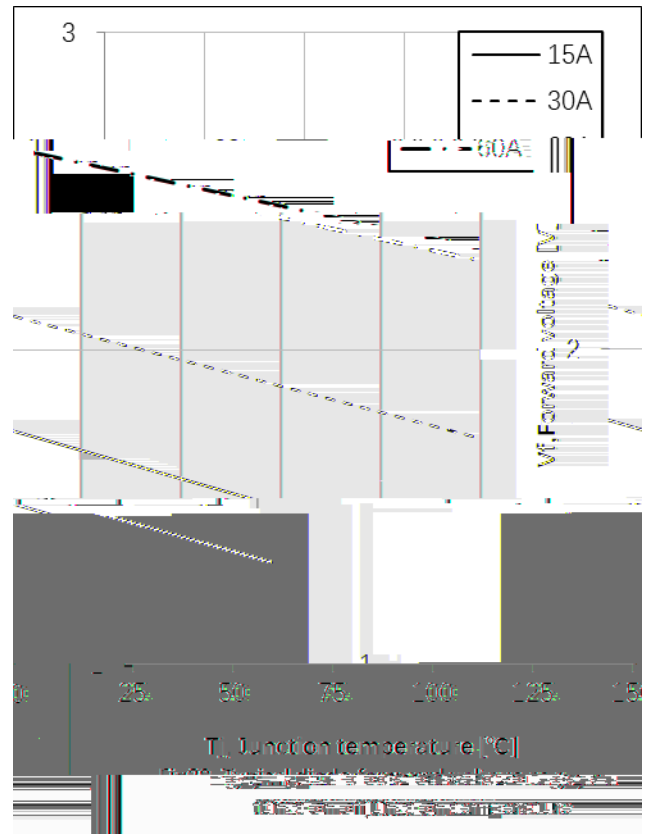
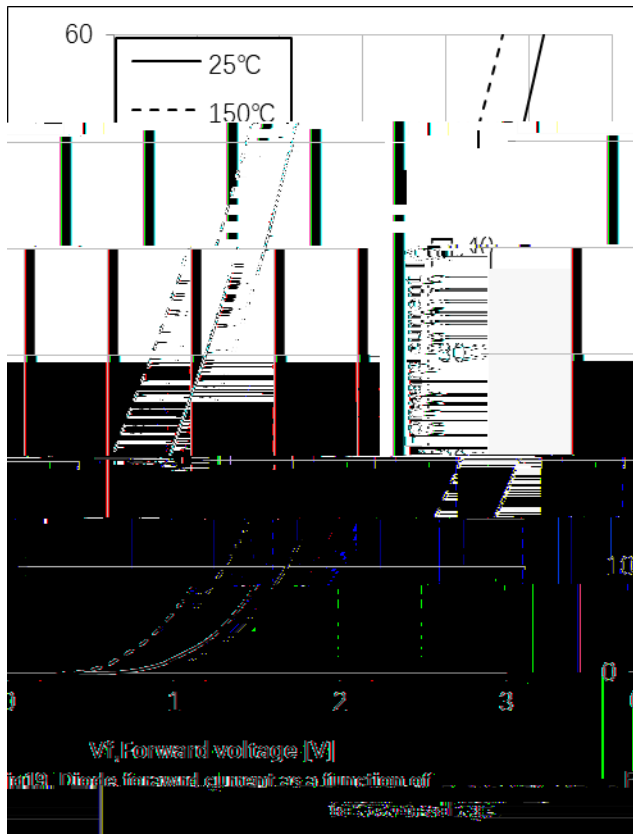
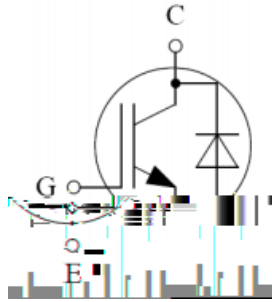
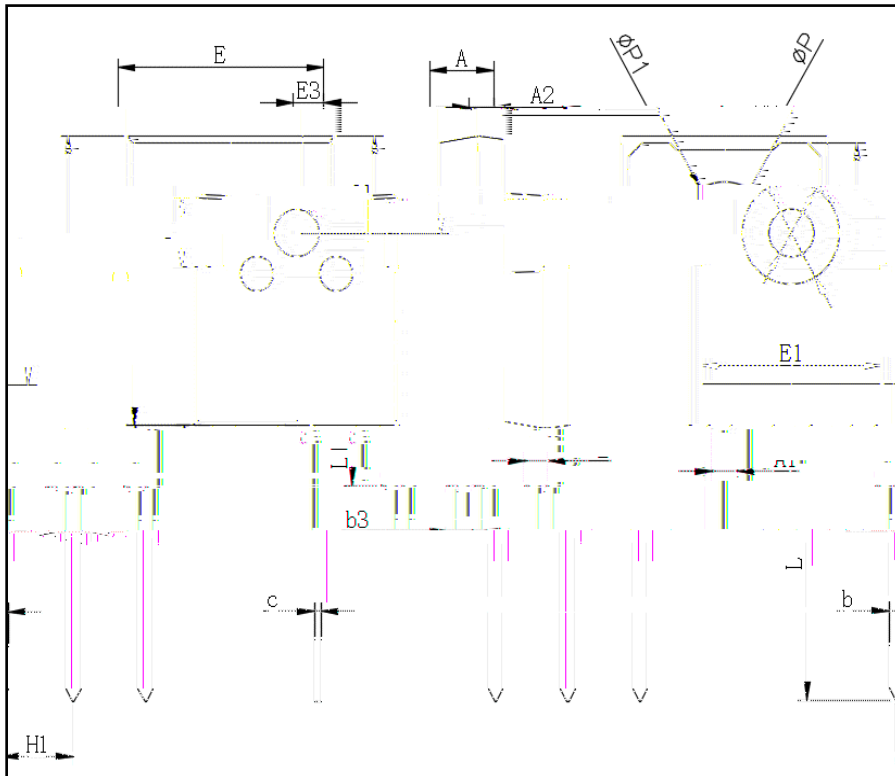


Fig 18. Diode Transient Thermal Impedance





## Package Outline Information



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
ΦP	3.40	3.80
ΦP1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20